

In re: Kim et al.
Serial No.: 10/054,540
Filed: January 22, 2002
Page 2 of 6

The list of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) An integrated circuit ferroelectric memory device, comprising:
 - an integrated circuit transistor having a source region and a drain region;
 - a ferroelectric capacitor on the integrated circuit transistor having first and second sidewalls, the ferroelectric capacitor including a first electrode adjacent the transistor, a second electrode remote from the transistor and a ferroelectric film therebetween;
 - a contact plug directly connected to the first electrode that electrically couples the ferroelectric capacitor to the source region of the integrated circuit transistor;
 - an insulating layer on the first and second sidewalls of the ferroelectric capacitor, the insulating layer having a surface that is substantially coplanar with an upper surface of the second electrode; and
 - a plate line directly on the ferroelectric capacitor.
2. (Original) A device according to Claim 1, wherein the plate line is directly on the second electrode of the ferroelectric capacitor.
3. (Original) A device according to Claim 1, wherein the integrated circuit ferroelectric memory device is free of a plug between the plate line and the second electrode.
4. (Original) A device according to Claim 3, wherein the integrated circuit ferroelectric memory device is free of an insulating layer between the plate line and the second electrode.
5. (Original) A device according to Claim 4, wherein the second electrode has a width and wherein the plate line is directly on the second electrode across the width.

In re: Kim et al.
Serial No.: 10/054,540
Filed: January 22, 2002
Page 3 of 6

6. (Original) A device according to Claim 1, further comprising a stripe line adjacent the second electrode and remote from the first electrode.

7. (Original) A device according to Claim 6, wherein the stripe line comprises aluminum.

8-9 (Cancelled).

10. (Original) A device according to Claim 1, wherein the first electrode comprises at least one of platinum and/or iridium dioxide.

11. (Original) A device according to Claim 1, wherein the ferroelectric film comprises at least one of PZT, SBT and/or BLT.

12. (Original) A device according to Claim 1, wherein the second electrode comprises at least one of iridium, ruthenium, platinum and/or iridium dioxide.

13-18 (Cancelled).